## **<u>MOSFET</u> – Power, Single,** N-Channel, μCool, UDFN6, 1.6x1.6x0.55 mm 30 V, 18 mΩ, 6.9 A

#### Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 1.6 x 1.6 x 0.55 mm for Board Space Saving
- Ultra Low R<sub>DS(on)</sub>
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

- · Power Load Switch
- Wireless Charging
- DC-DC Converters
- Motor Drive

### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V <sub>DSS</sub>	30	V
Gate-to-Source Volt	age		V <sub>GS</sub>	±20	V
Continuous Drain		$T_A = 25^{\circ}C$	۱ <sub>D</sub>	6.9	А
Current R <sub>θJA</sub> (Note 1, 3)	Steady State	$T_A = 85^{\circ}C$	]	5.0	
Power Dissipation $R_{\theta JA}$ (Note 1, 3)	Siale	$T_A = 25^{\circ}C$	P <sub>D</sub>	1.49	W
Continuous Drain Current R <sub>0.IA</sub>		$T_A = 25^{\circ}C$	Ι <sub>D</sub>	4.5	А
(Note 2, 3)	Steady	$T_A = 85^{\circ}C$		3.2	
Power Dissipation $R_{\theta JA}$ (Note 2, 3)	State	T <sub>A</sub> = 25°C	P <sub>D</sub>	0.64	W
Pulsed Drain Current $t_p = 10 \ \mu s$		I <sub>DM</sub>	20	А	
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			ΤL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient – Steady State (Note 1, 3)	$R_{\thetaJA}$	83.7	°C/W
Junction-to-Ambient – Steady State min Pad (Note 2, 3)	$R_{\theta JA}$	196.6	0/10

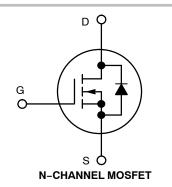
1. Surface-mounted on FR4 board using 1 in<sup>2</sup> pad size, 2 oz Cu pad.



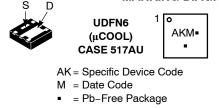
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MOSFET				
V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> MAX		
30 V	18 mΩ @ 10 V	6.9 A		
	26 mΩ @ 4.5 V	0.9 A		

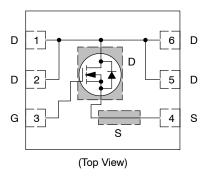


#### MARKING DIAGRAM



(Note: Microdot may be in either location)

PIN CONNECTIONS



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

2. Surface-mounted on FR4 board using the min pad size, 2 oz Cu pad.

The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
This device does not have ESD protection diode.

#### ELECTRICAL CHARACTERISTICS (T<sub>.1</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Units
OFF CHARACTERISTICS		-		-	-	-	-
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V,	, I <sub>D</sub> = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I <sub>D</sub> = 250 μ/	$I_D = 250 \ \mu A$ , ref to $25^{\circ}C$		14.2		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V,	$T_J = 25^{\circ}C$			1.0	μΑ
		$V_{DS} = 24 V$	T <sub>J</sub> = 125°C			10	1
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V	, V <sub>GS</sub> = 20 V			100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub>	<sub>3</sub> , I <sub>D</sub> = 250 μA	1.2		2.2	V
Negative Threshold Temp. Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μ.	A, ref to 25°C		-4.1		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.0 A		14	18	mΩ
		V <sub>GS</sub> = 4.5	V, I <sub>D</sub> = 5.0 A	1	20	26	1
Forward Transconductance	<b>9</b> FS	V <sub>DS</sub> = 1.5	V, I <sub>D</sub> = 5.0 A		16		S
CHARGES & CAPACITANCES		•			•		
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 15 V			400		pF
Output Capacitance	C <sub>OSS</sub>				215		
Reverse Transfer Capacitance	C <sub>RSS</sub>				21		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 15 V; I <sub>D</sub> = 5.0 A			3.7		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>				0.6		
Gate-to-Source Charge	Q <sub>GS</sub>				1.3		
Gate-to-Drain Charge	Q <sub>GD</sub>				1.2		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V; I <sub>D</sub> = 5.0 A			8		nC
SWITCHING CHARACTERISTICS, VG	S = 4.5 V (Note 6)						
Turn-On Delay Time	t <sub>d(ON)</sub>				9		ns
Rise Time	t <sub>r</sub>	$V_{CS} = 4.5$	/, V <sub>DD</sub> = 15 V,		15		
Turn-Off Delay Time	t <sub>d(OFF)</sub>		A, $R_G = 6 \Omega$		11		
Fall Time	t <sub>f</sub>	1		<u> </u>	2.5		1
SWITCHING CHARACTERISTICS, VG	S = 10 V (Note 6)			•			
Turn-On Delay Time	t <sub>d(ON)</sub>				6		ns
Rise Time	t <sub>r</sub>	$V_{CS} = 10 V_{CS}$	/ Vpp = 15 V.	<u> </u>	13		1
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$V_{GS}$ = 10 V, $V_{DD}$ = 15 V, $I_{D}$ = 5.0 A, $R_{G}$ = 6 $\Omega$		<u> </u>	14		1
Fall Time	t <sub>f</sub>			<u> </u>	2		1
DRAIN-SOURCE DIODE CHARACTER	ISTICS	•					
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V,	$T_J = 25^{\circ}C$		0.8	1.0	V
		$I_{\rm S} = 5.0 \rm{A}$			0.7		1

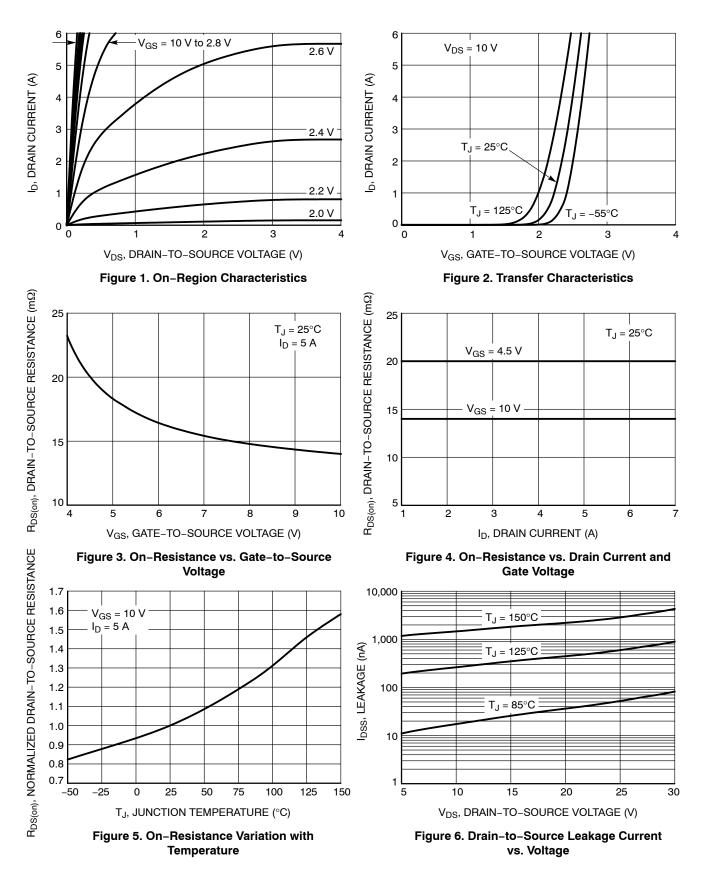
Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.

### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

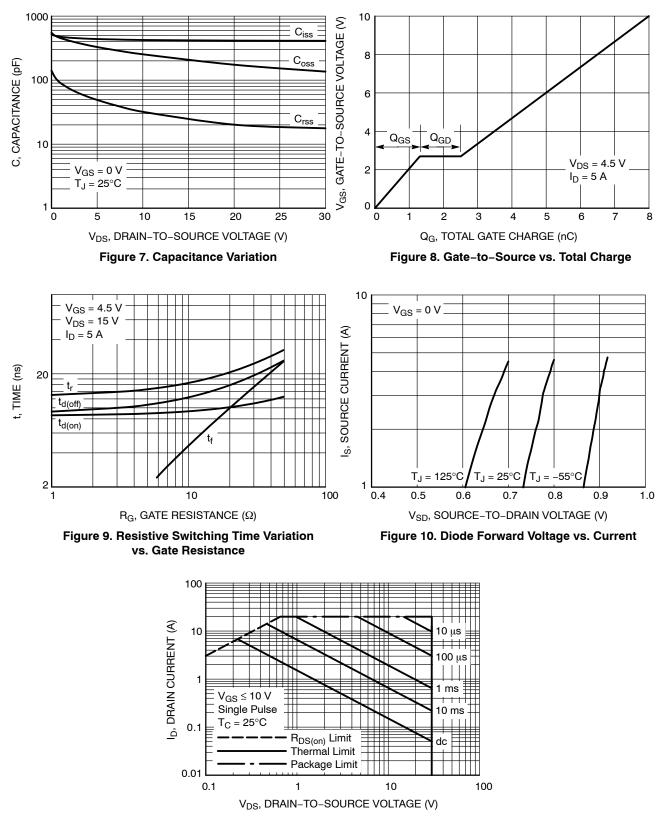
Parameter	Symbol	Test Condition	Min	Тур	Max	Units	
DRAIN-SOURCE DIODE CHARACTERISTICS							
Reverse Recovery Time	t <sub>RR</sub>			20		ns	
Charge Time	t <sub>a</sub>	$V_{GS}$ = 0 V, dls/dt = 100 A/µs, $I_S$ = 5.0 A		11			
Discharge Time	t <sub>b</sub>			10			
Reverse Recovery Charge	Q <sub>RR</sub>			8		nC	

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.

### **TYPICAL CHARACTERISTICS**



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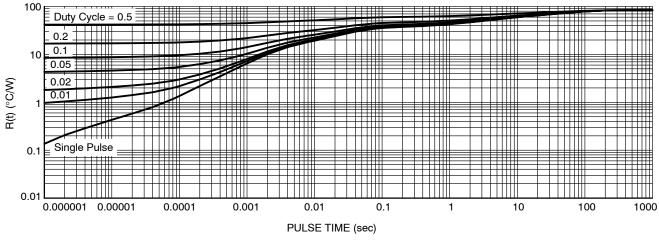
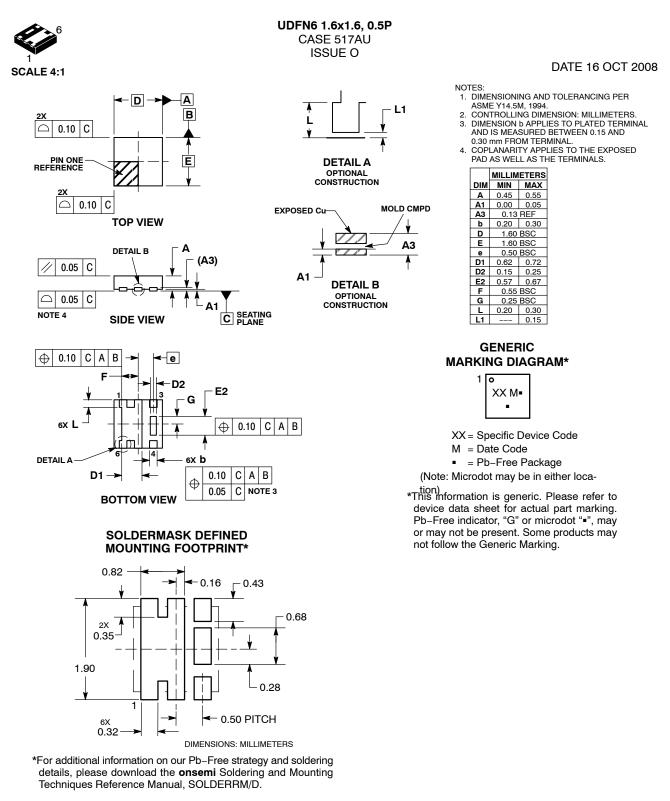


Figure 12. Thermal Response

### **DEVICE ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTLUS030N03CTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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DESCRIPTION:	UDFN6 1.6x1.6, 0.5P		PAGE 1 OF 1		

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